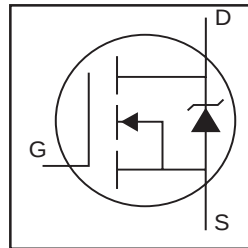


HEXFET® Power MOSFET Die in Wafer Form



200 V
Size 4.0
 $R_{ds(on)}=0.18\Omega$
5" Wafer

Electrical Characteristics (Wafer Form)

Parameter	Description	Guaranteed (Min/Max)	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	200V Min.	$V_{GS} = 0V, I_D = 100\mu A$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	0.180 Ω Max.	$V_{GS} = 10V, I_D = 10A$
$V_{GS(th)}$	Gate Threshold Voltage	2.3V Min., 4.0V Max.	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	25 μA Max.	$V_{DS} = 200V, V_{GS} = 0V, T_J = 25^\circ C$
I_{GSS}	Gate-to-Source Leakage	$\pm 10\mu A$ Max.	$V_{GS} = \pm 20V$
T_J	Operating Junction and	125 $^\circ C$ Max.	
T_{STG}	Storage Temperature Range		

Mechanical Data

Nominal Backmetal Composition, Thickness:	Cr-NiV-Ag (1kA°-2kA°-2.5kA°)
Nominal Front Metal Composition, Thickness:	99% Al, 1% Si (0.004 mm)
Dimensions:	0.147" x 0.201" (3.73mm x 5.11 mm)
Wafer Diameter:	125mm with 100 flat
Wafer thickness:	0.375mm + / -0.020mm
Relevant Die Mechanical Dwg. Number	01-5331
Minimum Street Width	0.084 mm
Reject Ink Dot Size	0.51mm Diameter Minimum
Recommended Storage Environment:	Store in original container, in dessicated nitrogen, with no contamination
Recommended Die Attach Conditions	For optimum electrical results, die attach temperature should not exceed 300C

Reference Standard IR packaged part (for design) : IRF640

Die Outline

